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9-11-02

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: T. SAITO et al.

Serial No.: 09/850,162

Filed: May 8, 2001

For: A SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND A
METHOD OF MANUFACTURING THE SAME

Group: 2812

Examiner: R. E. Pompey

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TECHNOLOGY CENTER 2800
SEP -6 2002**AMENDMENT**Assistant Commissioner For Patents
Washington, D.C. 20231

September 3, 2002

Sir:

In response to the Office Action dated April 1, 2002, the period of response for which extension is requested by the attached Petition for Extension of Time, please amend the above-identified application as follows:

IN THE CLAIMS:Please **amend** claims 1-5, 12, 15, 16, 17 and 39-42, as follows:

1. (Amended) A method for manufacturing a semiconductor integrated circuit device, comprising the steps of:
- (a) forming a groove for wiring in a first insulating film formed on a semiconductor substrate;
- (b) successively forming a barrier layer and a conductive film over said first insulating film including the inside of said groove for wiring and removing said